

# DECLARATION FOR PATENT APPLICATION

03S1578-1

As a below named inventor, I declare:  
that I verily believe myself to be the original, first and sole (if only one individual inventor is listed below) or an original, first and joint inventor (if more than one individual inventor is listed below) of the invention in

## NONVOLATILE MEMORY AND ERASING METHOD

the specification of which is attached hereto unless the following box is checked.

☐ was filed on \_\_\_\_\_ as United States Application  
or PCT International Application No. \_\_\_\_\_, and  
was amended on \_\_\_\_\_ (if applicable).

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information of which is material to patentability as defined in 37 CFR 1.56.

I hereby claim foreign priority benefits under 35 U. S. C. 119(a)-(d) or 365 (b) of any foreign application(s) for patent or inventor's certificate, or 35 U. S. C. 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed:

<u>Country</u>	<u>Category</u>	<u>Application No.</u>	<u>Filing Date</u>	<u>Priority Claim</u>
Japan	Patent	2003-372662	October 31, 2003	Yes

I hereby appoint the registrants of Oblon, Spivak, McClelland, Maier & Neustadt, P. C., 1940 Duke Street, Alexandria, Virginia 22314, Customer No. 22850, or any one of them. Send correspondence to Oblon, Spivak, McClelland, Maier & Neustadt, P. C., 1940 Duke Street, Alexandria, Virginia 22314, Telephone No. (703)413-3000.

I declare further that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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I declare further that my citizenship, residence and mailing address are as stated below next to my name:

Inventor: (Signature)DateResidence and mailing address

Tsuyoshi Tsujioka  
Tsuyoshi Tsujioka

Date: Feb. 10, 2004Citizen of: Japan

24-22, Nishiimagawa 3-chome,  
Higashisumiyoshi-ku,  
Osaka-shi, Osaka, Japan

Date:Citizen of: JapanDate:Citizen of: JapanDate:Citizen of: JapanDate:Citizen of: JapanDate:Citizen of: JapanDate:Citizen of: JapanDate:Citizen of: Japan

DOCKET NO.: 249189US2

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Tsuyoshi TSUJIOKA

SERIAL NO.: New Application

FILED: Herewith

FOR: NONVOLATILE MEMORY AND ERASING METHOD

**REQUEST FOR SMALL ENTITY STATUS**


This application qualifies for small entity status.

Respectfully Submitted,

OBLON, SPIVAK, McCLELLAND,  
MAIER & NEUSTADT, P.C.

Date: \_\_\_\_\_

2/23/04

  
\_\_\_\_\_  
Marvin J. Spivak

Registration No. 24,913

**C. Irvin McClelland**  
**Registration Number 21,124**

Customer Number

**22850**

Tel. (703) 413-3000  
Fax. (703) 413-2220  
(OSMMN 05/03)